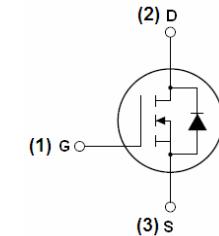


N-Channel Super Trench Power MOSFET

Description

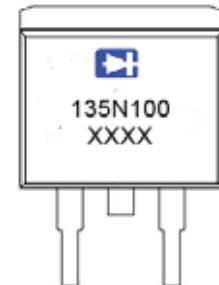
The RM135N100HD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.



Schematic diagram

General Features

- $V_{DS} = 100V, I_D = 135A$
- $R_{DS(ON)} < 4.6m\Omega$ @ $V_{GS} = 10V$
- Excellent gate charge $\times R_{DS(on)}$ product
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested



Marking and pin assignment



TO-263-2L top view

100% UIS TESTED!

Δ 100% Vds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
135N100	RM135N100HD	TO-263-2L	-	-	-

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous (Silicon Limited)	I_D	143	A
Drain Current-Continuous (Package Limited)	I_D	135	A
Drain Current-Continuous ($T_C=100^\circ\text{C}$)	$I_D(100^\circ\text{C})$	102	A
Pulsed Drain Current	I_{DM}	500	A
Maximum Power Dissipation	P_D	210	W
Derating factor		1.4	W/°C
Single pulse avalanche energy ^(Note 5)	E_{AS}	1050	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	0.71	°C/W
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Electrical Characteristics (T_C=25°C unless otherwise noted)

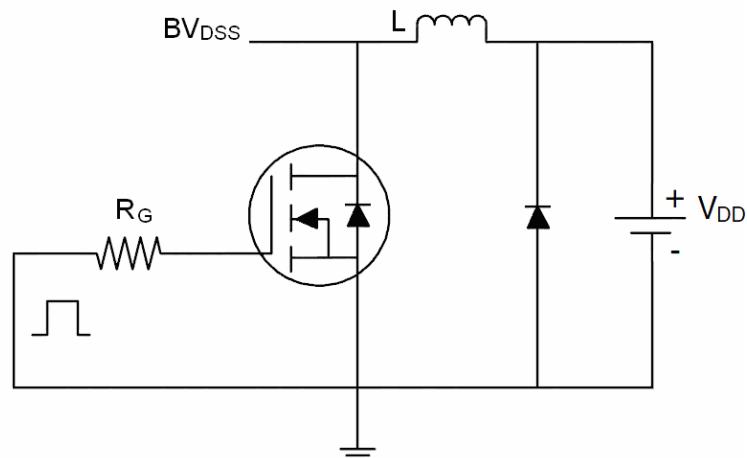
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =60A	-	3.8	4.6	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =60A	-	60	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	6400	-	PF
Output Capacitance	C _{oss}		-	731	-	PF
Reverse Transfer Capacitance	C _{rss}		-	35	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =60A V _{GS} =10V, R _G =4.7Ω	-	19	-	nS
Turn-on Rise Time	t _r		-	76	-	nS
Turn-Off Delay Time	t _{d(off)}		-	48	-	nS
Turn-Off Fall Time	t _f		-	14	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =60A, V _{GS} =10V	-	92	-	nC
Gate-Source Charge	Q _{gs}		-	35.4	-	nC
Gate-Drain Charge	Q _{gd}		-	18.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =135A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	135	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S di/dt = 100A/μs ^(Note 3)	-	63	-	nS
Reverse Recovery Charge	Q _{rr}		-	142	-	nC

Notes:

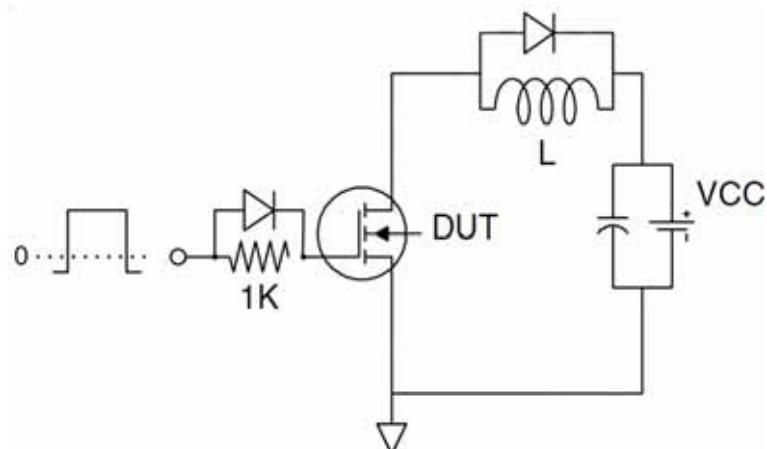
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_j=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25Ω

Test Circuit

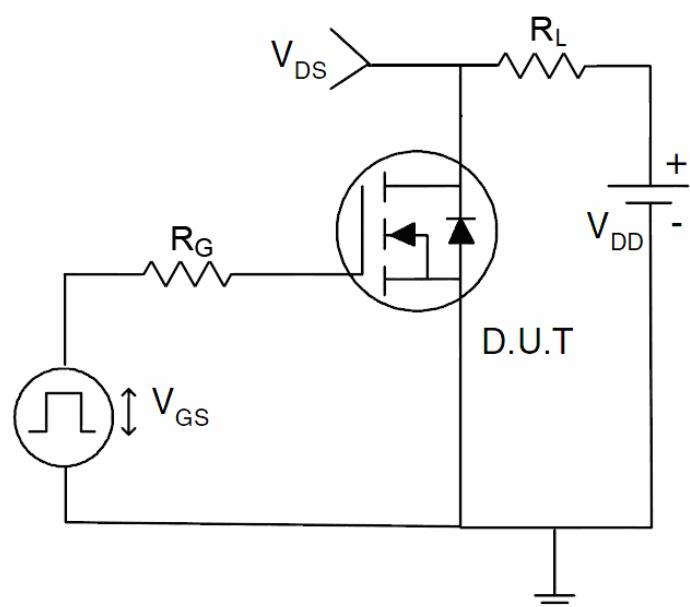
1) E_{AS} test Circuit



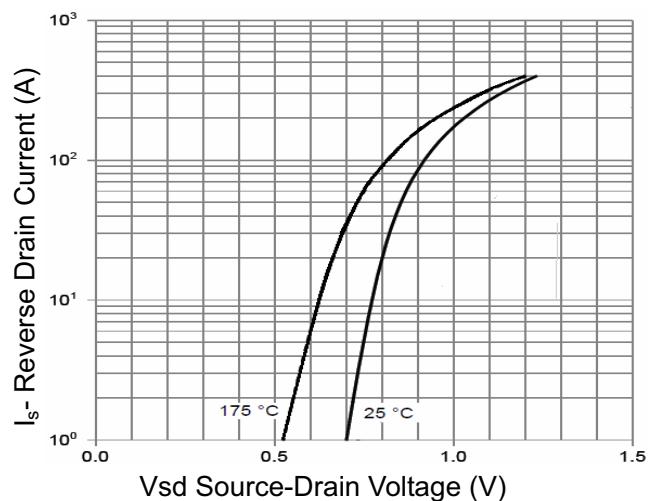
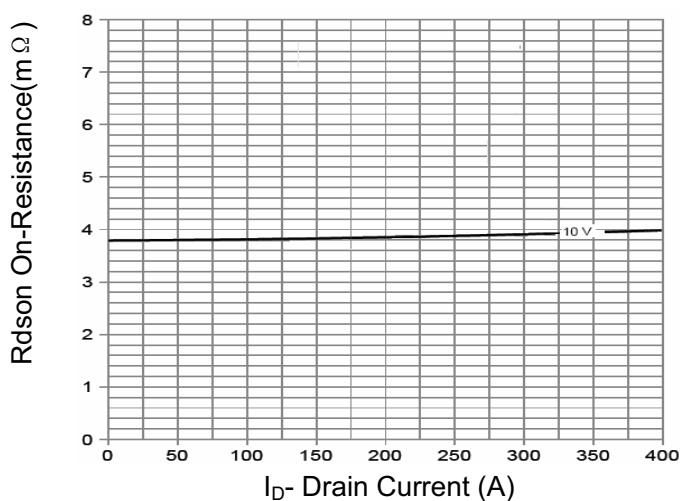
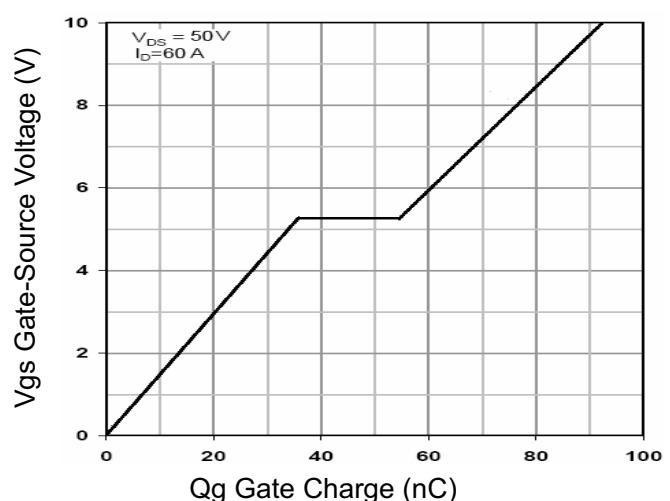
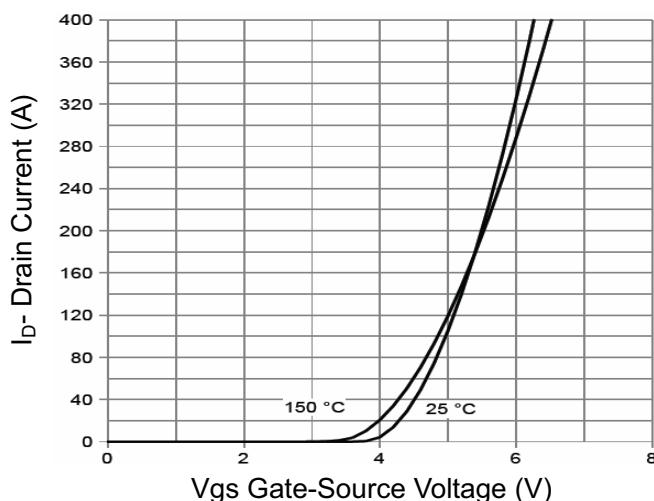
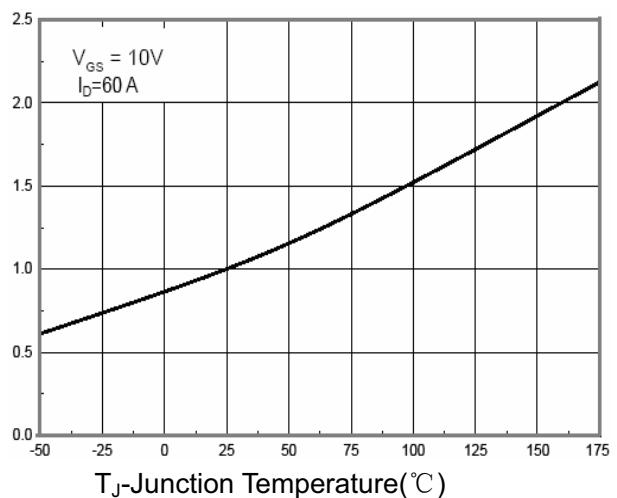
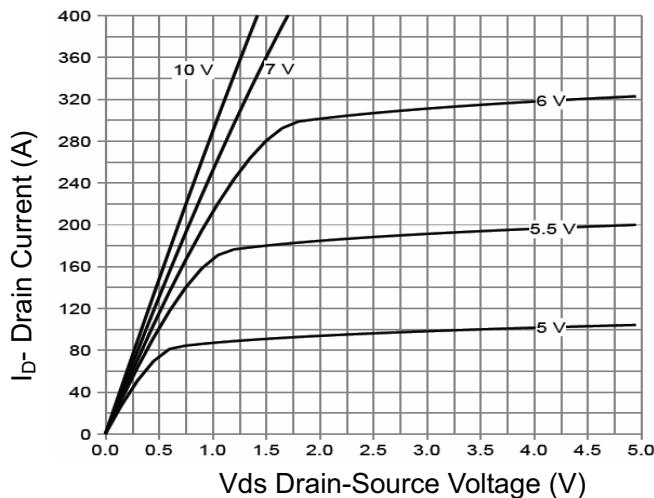
2) Gate charge test Circuit



3) Switch Time Test Circuit



RATING AND CHARACTERISTICS CURVES (RM135N100HD)



RATING AND CHARACTERISTICS CURVES (RM135N100HD)

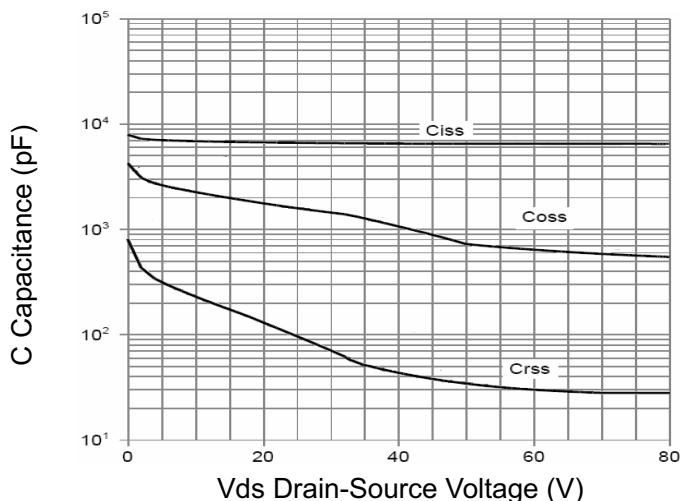


Figure 7 Capacitance vs Vds

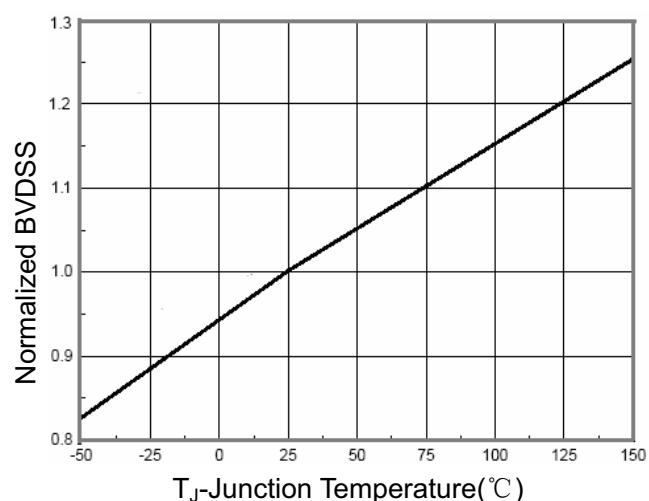


Figure 9 BV_{DSS} vs Junction Temperature

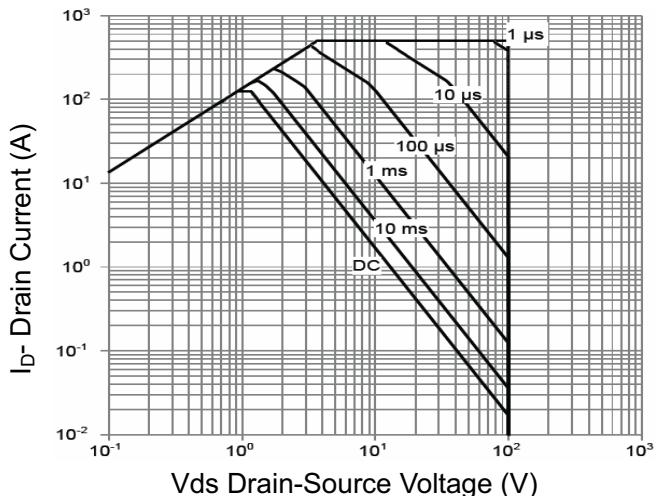


Figure 8 Safe Operation Area

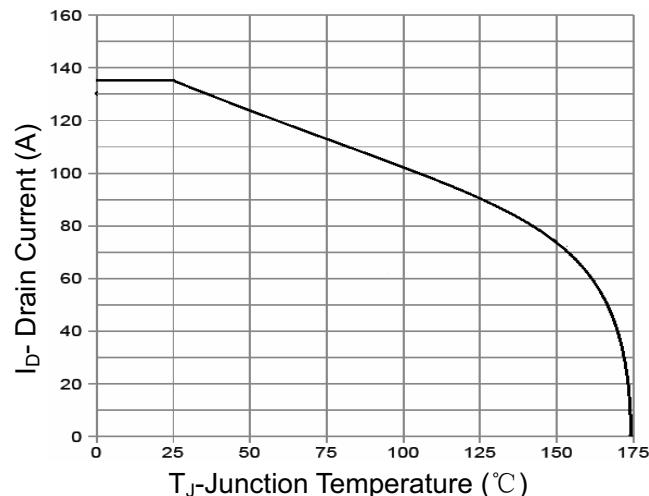


Figure 10 Current De-rating

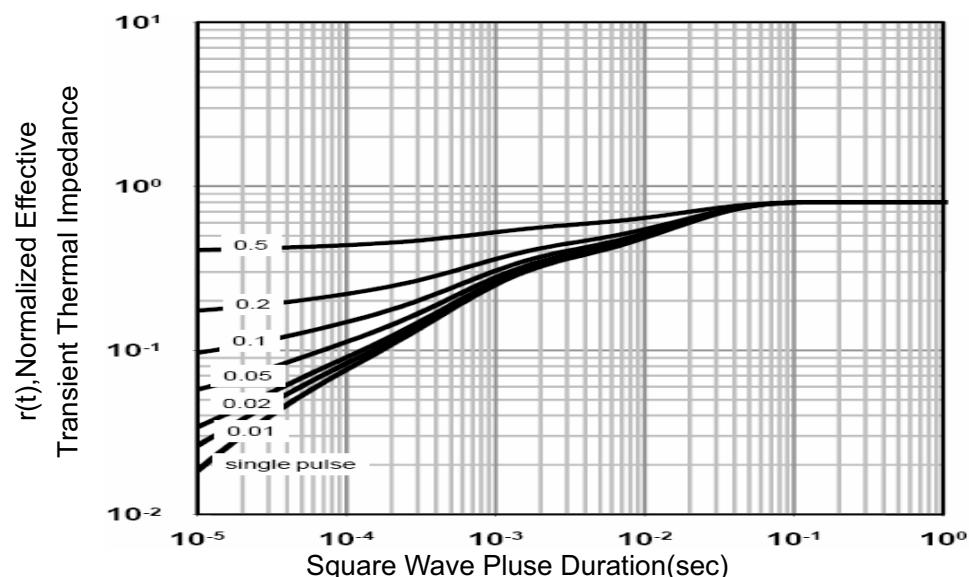
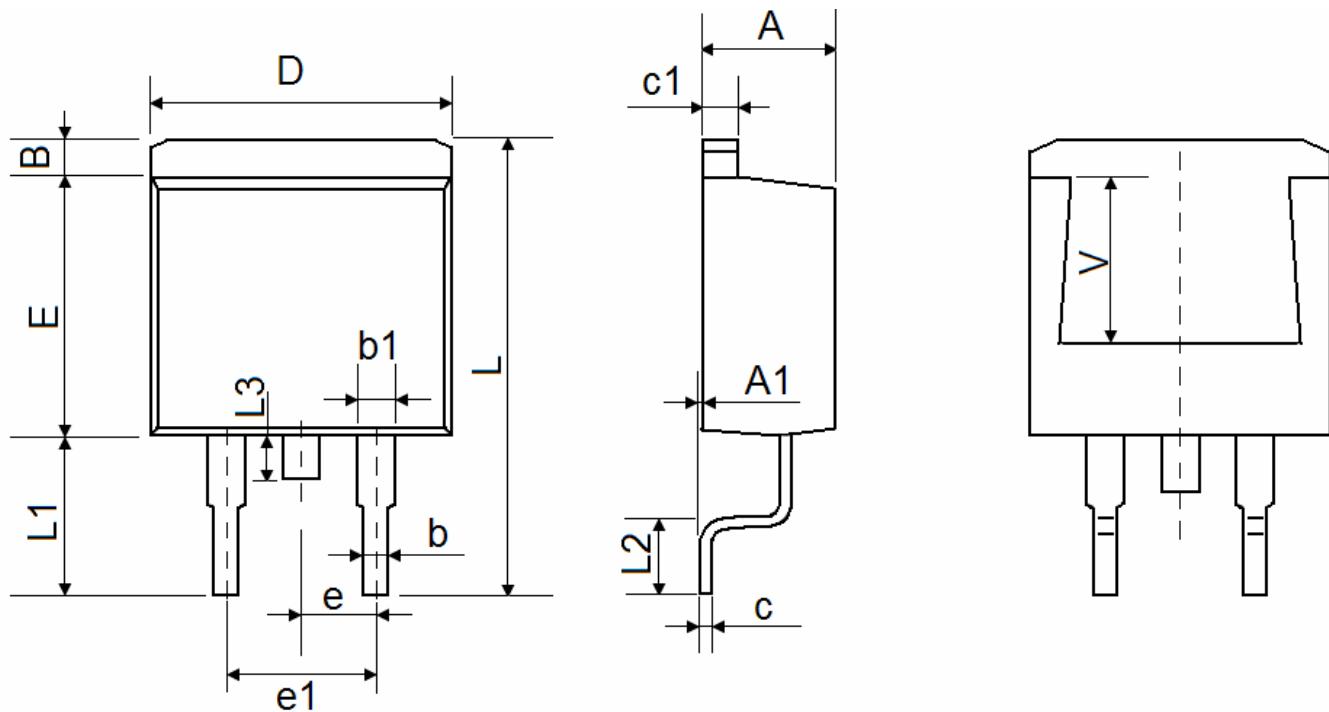


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	

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